

Octal 3-State Non-Inverting Buffer / Line Driver / Line Receiver in bare die form

Rev 1.0 24/04/19

Description

The 54AC244 is produced on a 1.5 μ m 5V CMOS process combining high speed LSTTL performance with CMOS low power. The device can be used as two 4-bit buffers or one 8-bit buffer & features non-inverting inputs with two output enables, each controlling four of the 3-state outputs. The device is designed to improve performance & density in clock drivers, 3-state memory address drivers & bus orientated transmitters and receivers. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} . Device inputs directly accept TTL without use of pull-up resistors.

Ordering Information

The following part suffixes apply:

- No suffix MIL-STD-883 /2010B Visual Inspection
- "H" MIL-STD-883 /2010B Visual Inspection+ MIL-PRF-38534 Class H LAT
- "K" MIL-STD-883 /2010A Visual Inspection (Space)
 + MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

For further information on LAT process flows see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

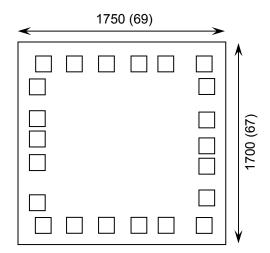
Supply Formats:

- Default Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Features:

- Outputs Source/Sink 24mA
- Low input current: 1µA
- 3-State outputs
- Outputs directly interface CMOS, NMOS and TTL
- Operating voltage range: 2.0V to 6.0V
- Lower power consumption & higher speed
- Function compatible with 54HC244
- Full military temperature range.

Die Dimensions in µm (mils)



Mechanical Specification

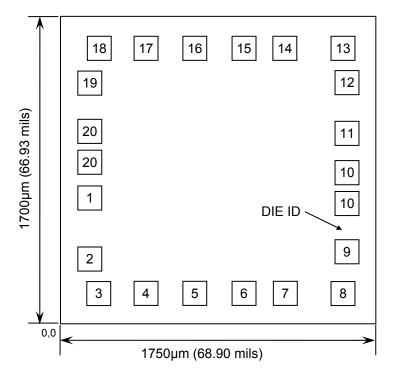
Die Size (Unsawn)	1750 x 1700 69 x 67	μm mils	
Minimum Bond Pad Size	130 x 130 5.12 x 5.12	μm mils	
Die Thickness	350 (±20) 13.78 (±0.79)	μm mils	
Top Metal Composition	Al 1%Si 1.1μ	m	
Back Metal Composition	ck Metal Composition N/A – Bare Si		



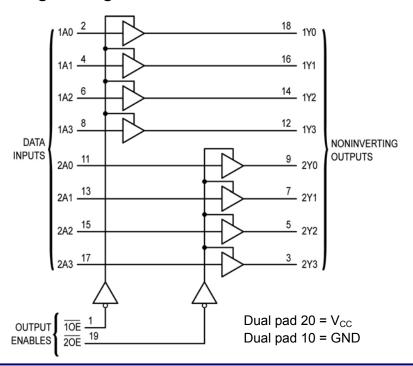


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Pad Layout and Functions



Logic Diagram



PAD	FUNCTION	COORDIN	ATES (mm)			
PAD	FUNCTION	Х	Y			
1	10E	0.100	0.630			
2	1A0	0.100	0.290			
3	2Y3	0.150	0.100			
4	1A1	0.410	0.100			
5	2Y2	0.680	0.100			
6	1A2	0.950	0.100			
7	2Y1	1.180	0.100			
8	1A3	1.500	0.100			
9	2Y0	1.520	0.330			
10	GND	1.520	0.600			
10	GND	1.520	0.770			
11	2A0	1.520	0.990			
12	1Y3	1.520	1.270			
13	2A1	1.500	1.460			
14	1Y2	1.180	1.460			
15	2A2	0.950	1.460			
16	1Y1	0.680	1.460			
17	2A3	0.410	1.460			
18	1Y0	0.150	1.460			
19	20E	0.100	1.270			
20	V _{CC}	0.100	1.000			
20	V _{CC}	0.100	0.830			
CONNECT CHIP BACK TO V _{CC} OR FLOAT						

Truth Table

INP	OUTPUTS	
10E 20E	1A, 2A	1Y, 2Y
L	L	L
L	Н	Н
Н	X	Z

H = High level (steady state)
L = Low level (steady state)
X = Don't care, Z = High impedance





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Pad Descriptions

ADDRESS INPUTS 1A0, 1A1, 1A2, 1A3, 2A0, 2A1, 2A2, 2A3 (Pads 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in non-inverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROL INPUTS 10E, 20E (Pads 1, 19)

Output enables (active—low). When a low level is applied to these pins, the outputs are enabled and the devices function as non-inverting buffers. When a high level is applied, the outputs assume the high impedance state.

OUTPUTS

1Y0, 1Y1, 1Y2, 1Y3, 2Y0, 2Y1, 2Y2, 2Y3 (Pads 18, 16, 14, 12, 9, 7, 5, 3)

Device outputs. Depending upon the state of the output- enable pins, these outputs are either non-inverting outputs or high-impedance outputs.

Absolute Maximum Ratings¹

	0)(117.01		
PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V _{CC}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V _{IN}	-0.5 to V _{CC} +0.5	V
DC Output Voltage (Referenced to GND)	V _{OUT}	-0.5 to V _{CC} +0.5	V
DC Input Current, per pin	I _{IN}	±20	mA
DC Output Current, per pin	I _{OUT}	±50	mA
DC V _{CC} or GND Current, per pin	I _{CC}	±50	mA
Power Dissipation in Still Air ²	P _D	750	mW
Storage Temperature Range	T _{STG}	-65 to 150	°C

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions³ (Voltages referenced to GND)

PARAMETEI	SYMBOL	MIN	MAX	UNITS	
DC Supply Voltage		V _{CC}	2.0	6.0	V
DC Input or Output Voltage		V_{IN} , V_{OUT}	0	V _{CC}	V
Operating Temperature Range		TJ	-55	+125	°C
Output current - High		I _{OH}	-	-24	mA
Output current - Low		I _{OL}	-	24	mA
Input Rise or Fall rate	V _{CC} = 3.0V		0	150	
$(V_{IN} \text{ from } 30\% \text{ to } 70\% \text{ V}_{CC})$	V _{CC} = 4.5V	Δt/ΔV	0	40	ns/V
(1114 3 33/3 63 / 3/3 4(2)	V _{CC} = 5.5V		0	25	

^{3.} This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND \leq (V_{IN} or V_{OUT}) \leq V_{CC} . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.





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DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	V _{cc} CONDITIONS	LIMITS			UNITS	
			CONDITIONS	25°C	85°C	FULL RANGE⁴	O.u.io
Minimum High-Level		3.0V	$V_{OUT} = 0.1 V \text{ or } V_{CC}$	2.1	2.1	2.1	
Input Voltage	V _{IH}	4.5V	-0.1V	3.15	3.15	3.15	V
		5.5V	-0.17	3.85	3.85	3.85	
Maximum Low-Level		3.0V	$V_{OUT} = 0.1 \text{V or } V_{CC}$	0.9	0.9	0.9	
Input Voltage	V _{IL}	4.5V	-0.1V	1.35	1.35	1.35	V
		5.5V	0.17	1.65	1.65	1.65	
		3.0V		2.9	2.9	2.9	
		4.5V	I _{OUT} = -50μA	4.4	4.4	4.4	V
Minimum High Lovel		5.5V		5.4	5.4	5.4	
Minimum High-Level Output Voltage	4	3.0V	$V_{IN} = V_{IL} \text{ or } V_{IH}^5$ $I_{OH} = -14\text{mA}$	2.56	2.46	2.40	V
		4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^{5}$	3.86	3.76	3.70	V
		5.5V	I _{OH} = -24mA	4.86	4.76	4.70	
	V _{OL}	3.0V	I _{OUT} = 50μA	0.1	0.1	0.1	V
		4.5V		0.1	0.1	0.1	
Maximum Low-Level		5.5V		0.1	0.1	0.1	
Output Voltage		3.0V	$V_{IN} = V_{IL} \text{ or } V_{IH}^5$ $I_{OL} = 12\text{mA}$	0.36	0.44	0.50	V
		4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^{5}$	0.36	0.44	0.50	V
		5.5V	I _{OL} = 24mA	0.36	0.44	0.50	
Maximum Input Leakage Current	I _{IN}	5.5V	V _{IN} = V _{CC} or GND	±0.1	±1.0	±1.0	μΑ
Maximum 3-State leakage current	I _{OZ}	5.5V	$V_{OUT}=V_{CC}$ or GND $V_{IN}=V_{IL}$ or V_{IH}	±0.5	±2.5	±5	μA
Minimum Dynamic	I _{OLD}	5.5V	V _{OLD} = 1.65V Max	-	75	50	mA
Output Current ⁶	I _{OHD}	5.5V	V _{OHD} = 3.85V Min	-	-75	-50	111/
Maximum Quiescent Supply Leakage Current	I _{CC}	5.5V	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$	8	40	80	μΑ

^{4.} -55° C ≤ T_{J} ≤ $+125^{\circ}$ C **5.** All outputs loaded; thresholds on input associated with output under test. **6.** Maximum test duration 2.0 ms, one output loaded at a time.





AC Electrical Characteristics⁷

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PARAMETER	SYMBOL	V _{cc} CONDITIONS	CONDITIONS	LIMITS			UNITS	
	OTIMBOL		25°C	85°C	FULL RANGE⁴	Oitiio		
	t _{PLH}	3.3V ±0.3	C _L = 50pF	9.0	10.0	12.5	ns	
Propagation Delay 1A to 1Y or 2A to 2Y	t _{PHL}	0.07 ±0.0	OL COPI	9.0	10.0	12.0	113	
(Figure 1)	t _{PLH}	5V ±0.5	C _L = 50pF	7.0	7.5	9.5	ns	
	t _{PHL}	0.0	or cob.	7.0	7.5	9.0	110	
	t _{PZH}	3.3V ±0.3	3 3\/ +0 3	C _L = 50pF	10.5	11.0	11.5	ns
Output Enable Time OE to 1Y or 2Y	t _{PZL}		.0 20.0	10.0	11.0	13	113	
(Figure 2)	t _{PZH}	5V ±0.5 C ₁ = 50pF	C _L = 50pF	7.0	8.0	9.0	ns	
	t _{PZL}	0 1 20.0	C _L = 50pF	8.0	8.5	10.5	115	
Output Disable Time OE to 1Y or 2Y	t _{PHZ}	3.3V ±0.3	C _L = 50pF	10.0	10.5	12.5	ns	
	t _{PLZ}		OL – 30pi	10.5	11.5	13.0	113	
	t _{PHZ}	5V ±0.5	0.5 C _L = 50pF		9.5	10.5	ns	
	t _{PLZ}	3 10.5	OL - 30pi	9	9.5	11	113	

^{7.} Not production tested in die form, characterized by chip design and tested in package.

Capacitance⁷

PARAMETER	SYMBOL	V _{cc}	CONDITIONS	TYPICAL	UNITS
Maximum Input Capacitance	C _{IN}	5.0V	T _J = 25°C	4.5	pF
Power Dissipation Capacitance (Per Buffer/Driver)	C _{PD}	5.0V	$T_J = 25$ °C, $C_L = 50$ pF, F = 1MHz	45	pF

Switching Waveforms

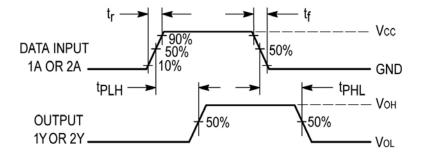


Figure 1 - Propagation Delay - Input 1A or 2A to Output 1Y or 2Y





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Switching Waveforms continued

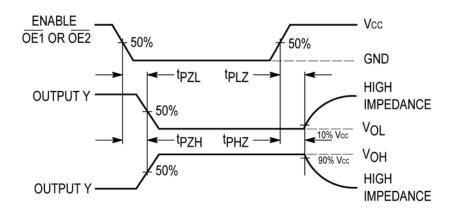
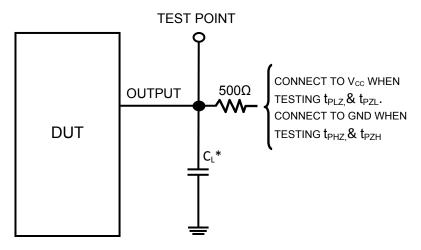


Figure 2 - Propagation Delay - Output Enable to Output 1Y or 2Y

Test Circuit



^{*} Includes all probe and jig capacitance

Figure 3

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